

METHOD OF FORMING MOS TRANSISTOR

ABSTRACT

Methods of simultaneously forming MOS transistors and a capacitor on a substrate having gate insulation layers of varying thicknesses are disclosed. A method includes forming field regions in a substrate to define a first transistor region, a capacitor region, and a second transistor region, forming a first gate stack in the first transistor region and a lower electrode in the capacitor region, and forming an upper electrode on the lower electrode with a dielectric layer interposed therebetween and a second gate stack in the second transistor region.